



BLV32F

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV32F** is Designed for in linear v.h.f. amplifiers of television transmitters and transporters.

FEATURES:

- Diffused emitter ballasting resistors
- $P_G = 16$ dB at 10 W/224 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB0}	60 V
V_{CEO}	32 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.1 °C/W

PACKAGE STYLE .500 6L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3,43	.160/4,06
B	.045/1,14	
C	.210/5,33	.220/5,59
D	.835/21,21	.865/21,97
E	.200/5,08	.210/5,33
F	.490/12,45	.510/12,95
G	.003/0,08	.007/0,18
H	.125/3,18	
I	.720/18,29	.730/18,54
J	.970/24,64	.980/24,89
K	.095/2,41	.105/2,67
L	.150/3,81	.170/4,32
M	.280/7,11	

1= Collector 2= Base 3 and 4= Emitter

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	32			V
BV_{CES}	$I_C = 15$ mA	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 32$ V			5.0	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 1.6$ A	20		120	---
C_C	$V_{CB} = 25$ V $f = 1.0$ MHz		50		pF
P_G	$V_{CE} = 25$ V $P_{OUT} = 10$ W $f = 224$ MHz	16			dB

